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dN/dx simulation software in CEPCSW

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Motivation

- The particle identification is very important for CEPC flavor physics study. Good hadron separation up to 20 GeV is essential
- Traditionally: using dE/dx method
 - Due to the production of delta electron, the deposited energy follows Landau distribution
 - Resolution is ~6%
- New technique: using dN/dx (cluster counting) method
 - The number of primary ionization follows Poisson distribution
 - Resolution could reaches <3%</p>
- The dN/dx technique will be widely explored in CEPC drift chamber detector



Ionization simulation in gas

- □ Garfield++
 - Using Heed PAI model to simulate the ionization in gas precisely
 - Can simulate the drift and avalanche of electrons in gas
 - **The drift of ions to cathode can be simulated**
 - The induced current can be given
 - It is useful to study and characterize the properties of gas detector with simple geometry but not for full drift chamber detector

Geant4

- Can simulate collider events and the interaction between particles and materials in full detector
- It does not simulate the ionization process properly, neither the drift and avalanche processes
- In order to simulate including particle interaction will detector materials, ionization in gas, drift and avalanche processes in full detector, we try to combined Geant4 and Garfield++ in CEPCSW3

CEPCSW for drift chamber study

- Framework:
 - Gaudi
- EDM:
 - EDM4hep
 - FWCore
- Detector geometry and B field:
 - DD4hep
 - GeomSvc
- Drift chamber:
 - DC simulation (Geant4)
 - DC digitization
 - Track reconstruction (Genfit)
 - dN/dx simulation (Garfield++)
 - dN/dx reconstruction



Scheme of dN/dx study in CEPCSW



Ionization simulation in CEPCSW (G4 PAI)

- First try: according to paper <u>"Interfacing Geant4, Garfield++ and</u> <u>Degrad for the Simulation of Gaseous Detectors"</u>
 - Geant4 PAI model to simulate primary or secondary ionization
 - TrackHeed to simulate ionization from residual delta electron
- However, it was found that the primary ionization produced by this method is much less than Garfield++.



Checking with authors:

- This method designed to obtain correct energy deposition (or total ionizations)
- It is true that this method will give less primary ionizations, so this method is obsoleted

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Ionization simulation in CEPCSW (TrackHeed)

Current method:

- The simulation of ionization is done by TrackHeed same as Garfield++
- The particle related information is provided by Geant4, e.g. particle type, initial position and momenta, ionization path length
- TrackHeedSimTool is created for this task
 - Input: G4Step
 - Use TrackHeed to simulate one step length (or multi-step length for speed up) ionization (new API added to Garfield++ PR)
 - Output: cluster and total ionization information (contains position, time, cell id), saved in SimTrackerHit collection
 - The kinetic energy of G4Track will be updated according to the energy loss in the ionization
 - Non-uniform magnetic field can be handled easily

Ionization simulation performance

♦ Gas: 50% He + 50 % C₄H₁₀



Ionization simulation performance

Gas: 50% He + 50 % C₄H₁₀



Signal simulation in CEPCSW

- From ionized electrons to induced currents
 - Using Garfield++, simulate the drift and avalanche of electron and drift of ions. It is slow, O(1) to O(10) seconds for different gas for one electron
 - Going to use parameterization method (parameters are based on Garfield++ simulation results), will be much faster
 - For each electron, give one induced current spectrum
 - As done by Garfield++, stacking all spectrums which come from same drift chamber cell gives final induced current for this cell



Getting parameters from Garfield++

- Garfield++ simulation:
 - 500k electrons uniformly distributed $1 \times 1 \text{ cm}^2$ drift chamber cell
 - Gas: 50% He + 50 % C₄H₁₀
 - Center signal wire (2000 V), eight field wires (0 V)









One electron drift and avalanche

Ions drift

Getting parameters from Garfield++

✤ After some studies, it is shown that if we shift the peak position of induced current spectrum to same value (e.g. 100 ns) and scale the peak value to same value (e.g. 2 × 10⁻³), the spectrums are similar



Simulating induced current ≈ simulating (peak_time, peak_value)
+ using induced current template

Garfield++ simulation



- Simulate (peak_time, peak_value):
 - Sampling method base on which bin the electron (x,y) is located
 - Machine learning method according electron (x, y) without binning ¹³

Summary and Plan

- A scheme of dN/dx study in CEPCSW has been presented
- The ionization simulation using Geant4 combined with TrackHeed have been implemented in CEPCSW. Results are consistent with Garfield++ simulation
- In order to speed up the avalanche simulation, a parameterized method has been studied and working in progress
- **G** Future plan:
 - Extend EDM4hep to store waveform information (cell id, vector pairs of charge and time)
 - Electronics simulation software to be added in CEPCSW
 - Developing peak finding algorithm

